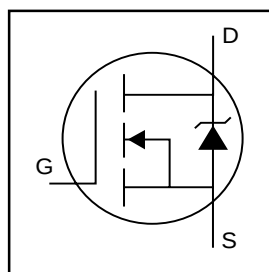


IRL3103S IRL3103L

- Advanced Process Technology
- Surface Mount (IRL3103S)
- Low-profile through-hole (IRL3103L)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

HEXFET® Power MOSFET



$$V_{DS} = 30V$$

$$R_{DS(on)} = 12m\Omega$$

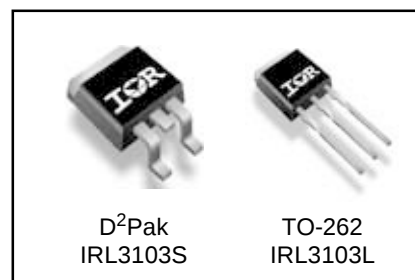
$$I_D = 64A$$

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRL3103L) is available for low-profile applications.



D²Pak
IRL3103S

TO-262
IRL3103L

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	64	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	45	
I_{DM}	Pulsed Drain Current ①	220	
P_D @ $T_C = 25^\circ C$	Power Dissipation	94	W
	Linear Derating Factor	0.63	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
I_{AR}	Avalanche Current①	34	A
E_{AR}	Repetitive Avalanche Energy①	22	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

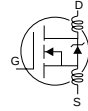
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.6	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	40	

IRL3103S/IRL3103L

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.028	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	12	$m\Omega$	$V_{GS} = 10V, I_D = 34A$ ④
		—	—	16		$V_{GS} = 4.5V, I_D = 28A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	22	—	—	S	$V_{DS} = 25V, I_D = 34A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	33	nC	$I_D = 34A$
Q_{gs}	Gate-to-Source Charge	—	—	5.9		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	17		$V_{GS} = 4.5V$, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	—	8.9	—		$V_{DD} = 15V$
t_r	Rise Time	—	120	—		$I_D = 34A$
$t_{d(off)}$	Turn-Off Delay Time	—	14	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	9.1	—		$V_{GS} = 4.5V$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1650	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	650	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$, See Fig. 5
E_{AS}	Single Pulse Avalanche Energy②	—	1320⑤	130⑥	mJ	$I_{AS} = 34A, L = 0.22mH$



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	64	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)①	—	—	220		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 34A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	57	86	ns	$T_J = 25^\circ\text{C}, I_F = 34A$
Q_{rr}	Reverse Recovery Charge	—	110	170	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 220\mu H$
 $R_G = 25\Omega$, $I_{AS} = 34A$, $V_{GS} = 10V$ (See Figure 12)
- ③ $I_{SD} \leq 34A$, $di/dt \leq 120A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$

④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to $T_J = 175^\circ\text{C}$.

**When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

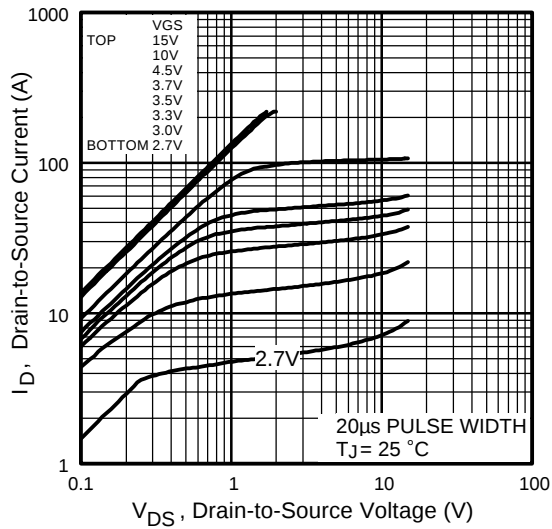


Fig 1. Typical Output Characteristics

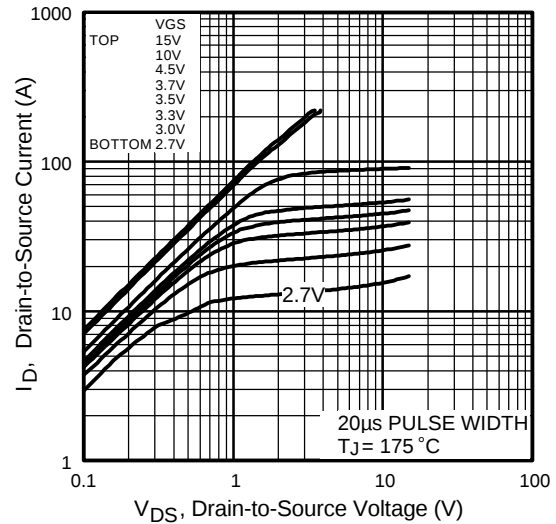


Fig 2. Typical Output Characteristics

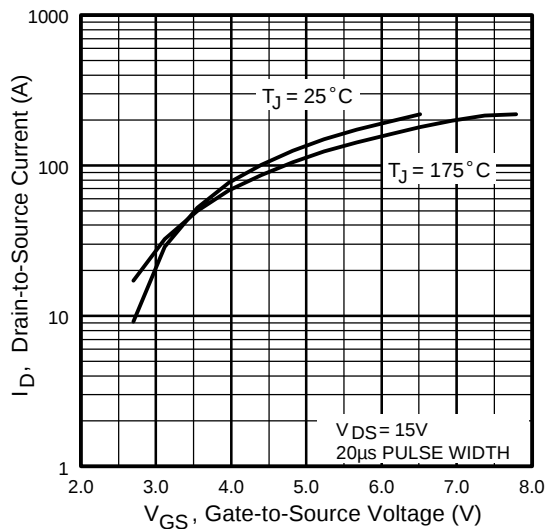


Fig 3. Typical Transfer Characteristics

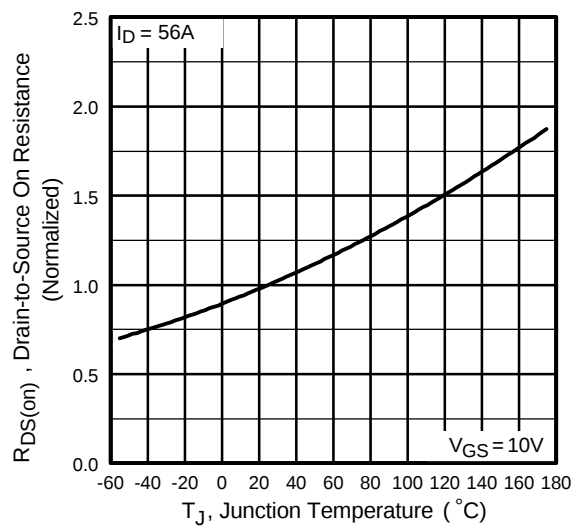
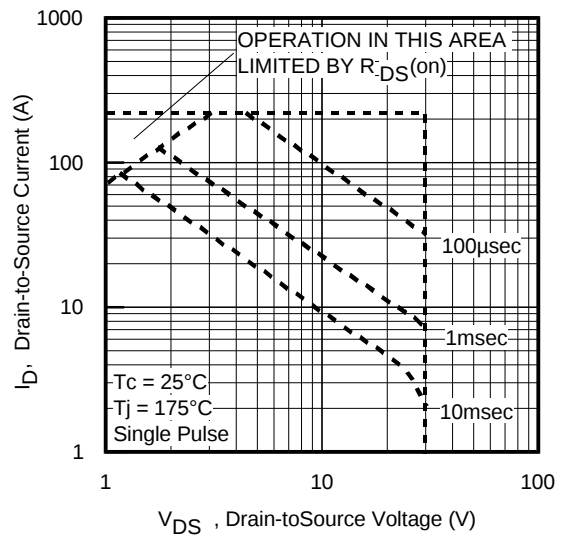
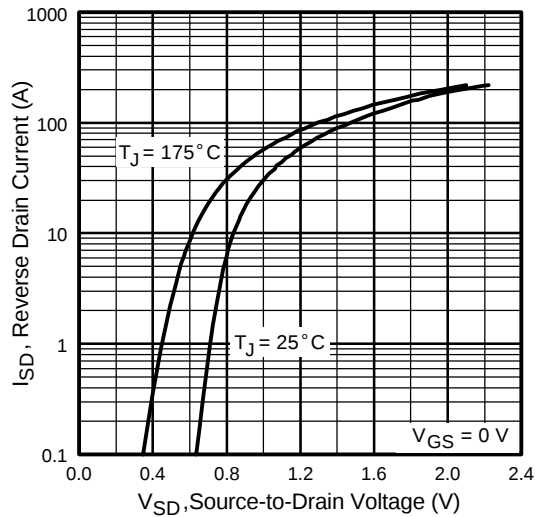
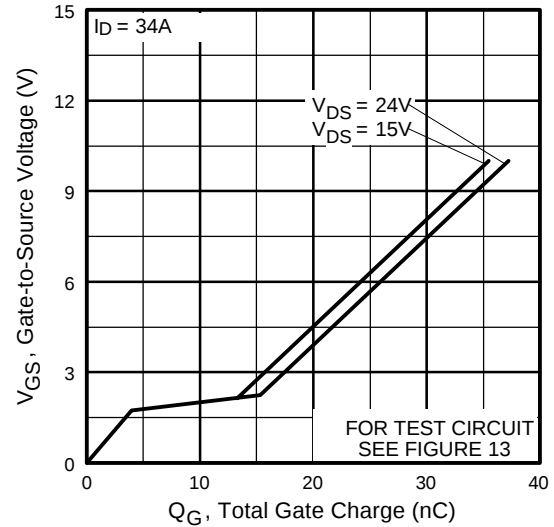
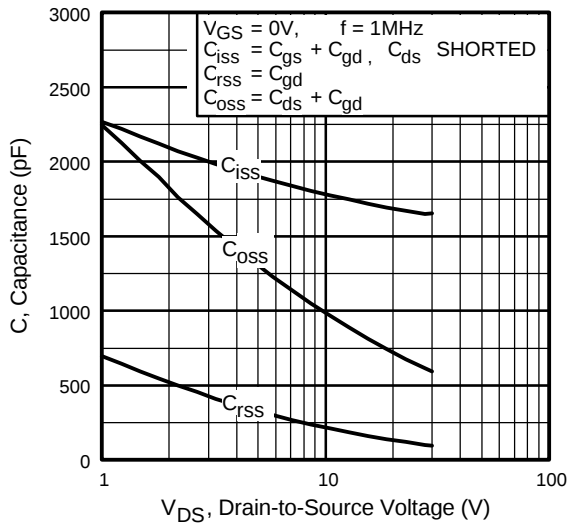


Fig 4. Normalized On-Resistance Vs. Temperature

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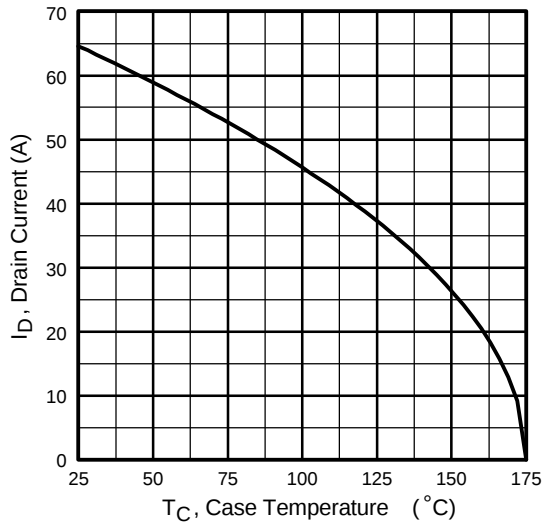


Fig 9. Maximum Drain Current Vs. Case Temperature

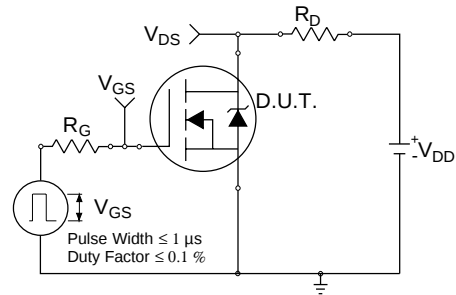


Fig 10a. Switching Time Test Circuit

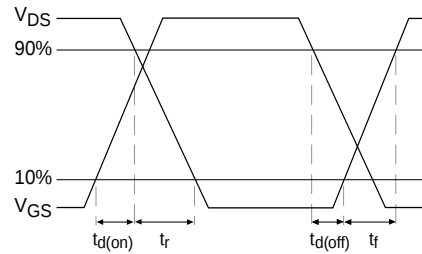


Fig 10b. Switching Time Waveforms

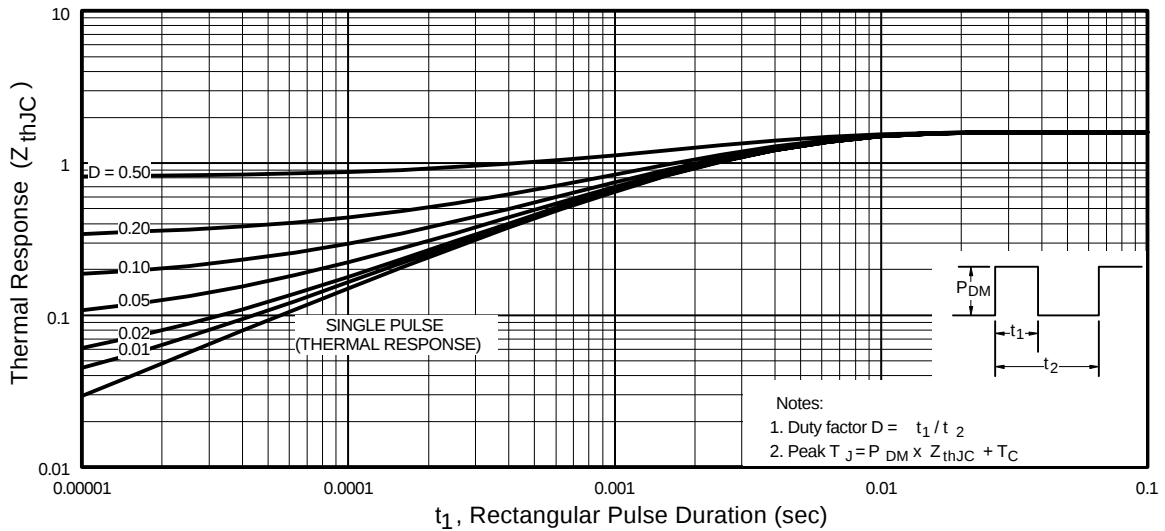


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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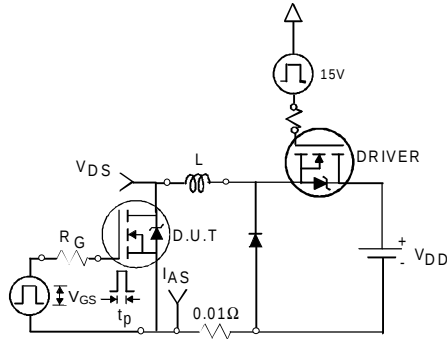


Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms

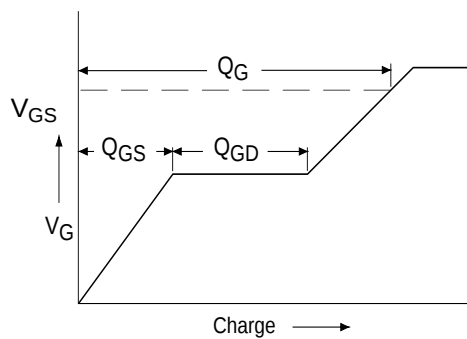


Fig 13a. Basic Gate Charge Waveform

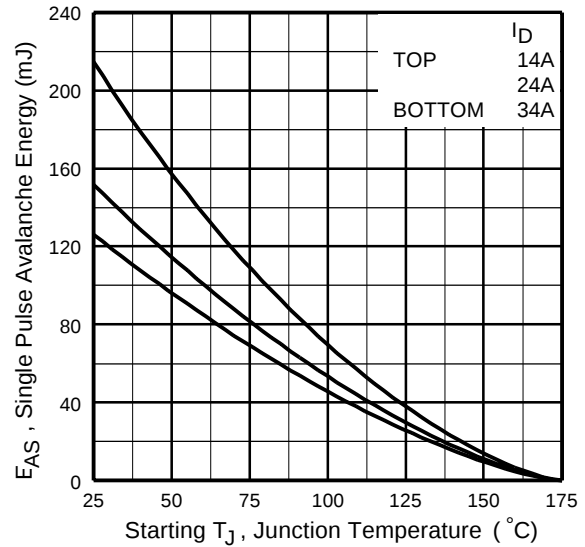


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

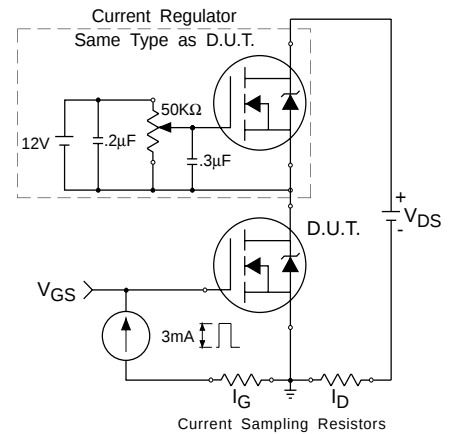
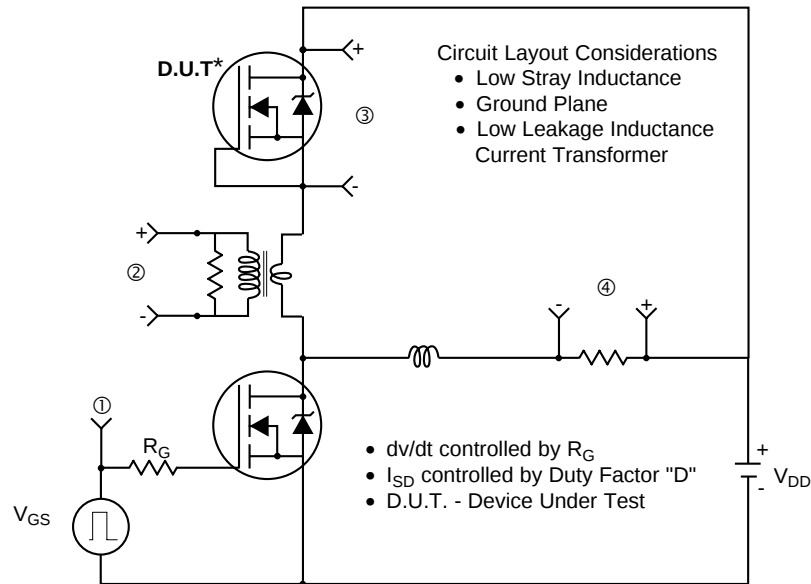
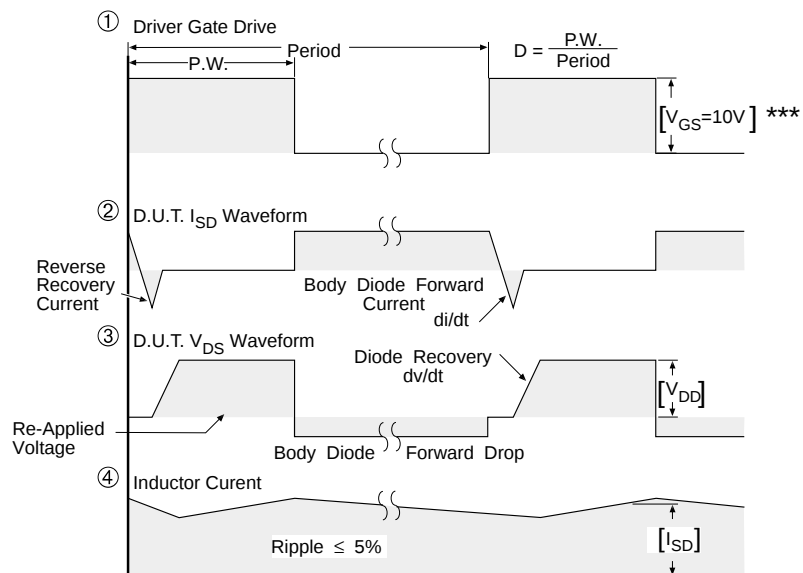


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



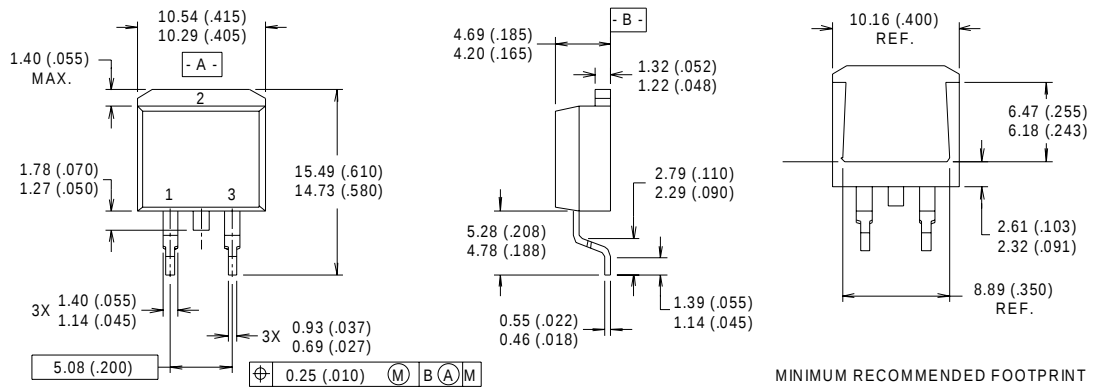
*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For N-channel HEXFET® power MOSFETs

IRL3103S/IRL3103L

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D²Pak Package Outline



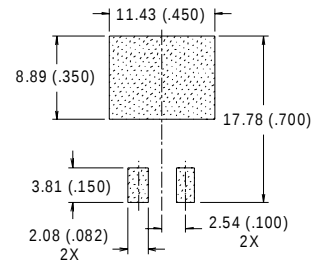
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

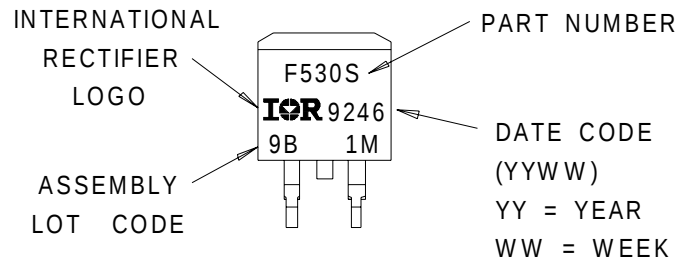
LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

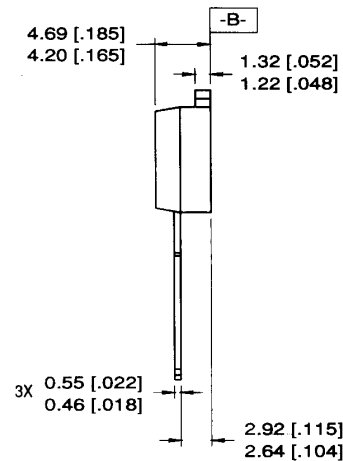
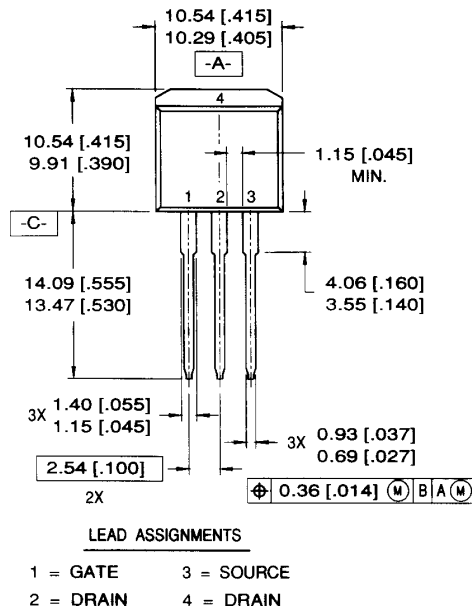
MINIMUM RECOMMENDED FOOTPRINT



D²Pak Part Marking Information



TO-262 Package Outline

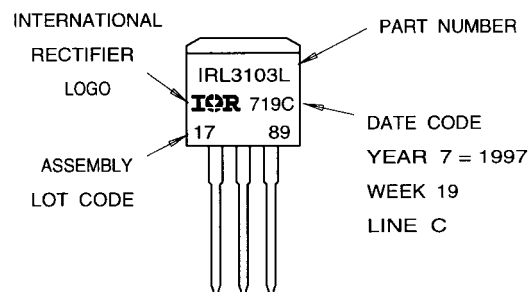


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

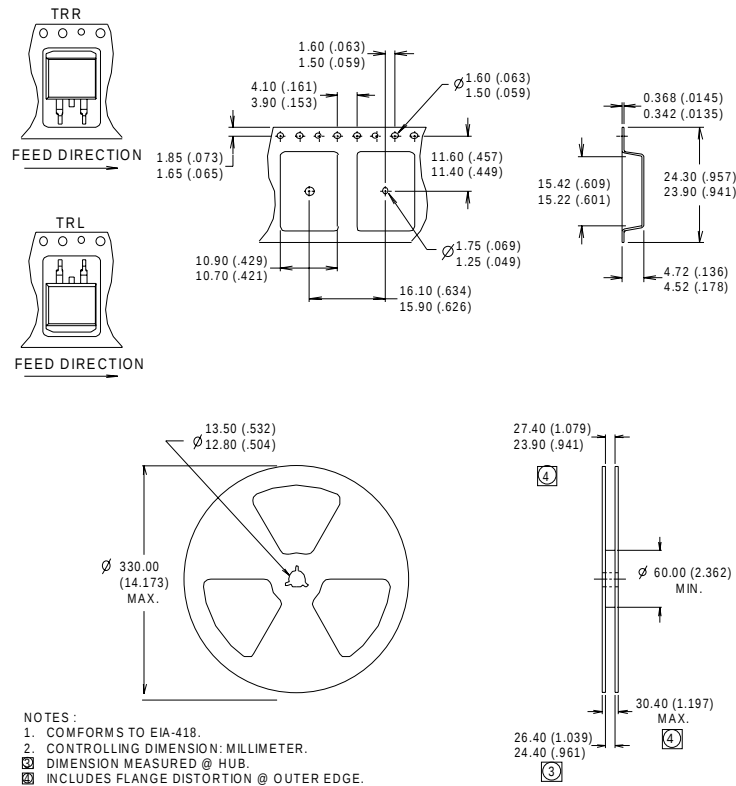
EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



IRL3103S/IRL3103L

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D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

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TAC Fax: (310) 252-7903

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